

Description

The AO3406 uses advanced trench technology

to provide excellent $R_{\text{DS}(\text{ON})},$ low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



General Features

 $V_{DS} = 30V I_{D} = 5.8A$

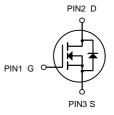
 $R_{DS(ON)}$ < 28m Ω @ V_{GS}=10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AO3406	SOT-23-3L	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

symbol	parameter		unit
V _{DS}	Drain-source voltage		V
V _G S	Gate-source voltage		V
ID	Drain current-continuous³@Tj=125℃		А
IDM	-pulse <i>d</i> ^b	20	А
Is	Drain-source Diode forward current		А
P _D	Maximum power dissipation		W
Tj	Operating junction Temperature range		°C
Rth JA	Thermal Resistance junction-to ambient	100	°C/W



Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Condition	Min	Тур	Max	Unit
BV _{DSS}	V _{GS} =0V, I _D =250μA	30	-	-	V
IDSS	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
IGSS	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
VGS(th)	V _{DS} =V _{GS} , I _D =250μA	0.8	1.4	2.2	V
	V _{GS} =10V, I _D =5A	-	24	28	
RDS(ON)	V _{GS} =4.5V, I _D =4A		26	32	mΩ
gfs	V _{GS} =5V, I _D =5A	-	33	-	S
Ciss	Vps=15V Vcs=0V		255		pF
coss	f=1.0MHz		45		
CRSS	_		35		
tD(ON)		-	4.5	-	ns
tr	V _{DS} =15V V _{GS} =10V	-	2.5	-	
tD(OFF)	R _L =2.6 ohm R _{GEN} =3ohm	-	14.5	-	
tf		-	3.5	-	
Qg		-	5.2	-	
Qgs	V _{DS} =15V,I _D =5.8A	-	0.85	-	nC
Qgd	VGS=1UV	-	1.3	-	
V _{SD}	V _{GS} =0V,Is=1A	-	0.76	1.16	V
	BV _{DSS} IDSS IGSS VGS(th) RDS(ON) gfs Ciss COSS CRSS tD(ON) tr tD(OFF) tf Qg Qgs Qgd	BV _{DSS} V _{GS} =0V, I _D =250μA IDSS V _{DS} =30V, V _{GS} =0V IGSS V _{DS} =0V, V _{GS} =±20V VGS(th) V _{DS} =V _{GS} , I _D =250μA V _{GS} =10V, I _D =5A V _{GS} =4.5V, I _D =4A V _{GS} =5V, I _D =5A C _{ISS} V _{DS} =15V, V _{GS} =0V CCSS tD(ON) tr V _{DS} =15V V _{GS} =10V R _L =2.6 ohm R _{GEN} =3ohm tf Qg Qgs V _{DS} =15V, I _D =5.8A V _{GS} =10V Qgd V _{DS} =10V Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd Qgd	BV _{DSS} V _{GS} =0V, I _D =250μA 30 IDSS V _{DS} =30V, V _{GS} =0V - IGSS V _{DS} =0V, V _{GS} =±20V - VGS(th) V _{DS} =V _{GS} , I _D =250μA 0.8 RDS(ON) V _{GS} =10V, I _D =5A - V _{GS} =4.5V, I _D =4A - C _{ISS} V _{DS} =15V,V _{GS} =0V f=1.0MHz CRSS tD(ON) - tr V _{DS} =15V V _{GS} =10V R _E =2.6 ohm R _{GEN} =3ohm - Qg - Qgs V _{DS} =15V,I _D =5.8A - Qgd - Qgd - Qgd - Qgd - Qgd - Qgd - COSS -	BV _{DSS} V _{GS} =0V, I _D =250μA 30 - IDSS V _{DS} =30V, V _{GS} =0V IGSS V _{DS} =0V, V _{GS} =±20V VGS(th) V _{DS} =V _{GS} , I _D =250μA 0.8 1.4 V _{GS} =10V, I _D =5A - 24 RDS(ON) V _{DS} =4.5V, I _D =4A 26 gfs V _{GS} =5V, I _D =5A - 33 Clss V _{DS} =15V, V _{GS} =0V f=1.0MHz 45 CRSS 35 tD(ON) - 4.5 tr V _{DS} =15V V _{GS} =10V R _L =2.6 ohm R _{GEN} =3ohm - 14.5 Qg - 5.2 Qgg V _{DS} =15V,I _D =5.8A V _{GS} =10V - 0.85 Qgd - 5.2 Qgd - 1.3	BVDSS VGS=0V, ID=250μA 30 1 IDSS VDS=30V, VGS=0V 1 IGSS VDS=0V, VGS=±20V ±100 VGS(th) VDS=VGS, ID=250μA 0.8 1.4 2.2 VGS=10V, ID=5A - 24 28 VGS=4.5V, ID=4A 26 32 GfS VGS=5V, ID=5A - 33 255 CISS VDS=15V, VGS=0V f=1.0MHz 45 CRSS

Notes:

- 1、surface mounted on FR4 board,t≤10sec
- 2、pulse test: pulse width≤300µs,duty≤2%
- $\ensuremath{\mathtt{3}}_{\times}$ guaranteed by design, not subject to production testing



Typical Performance Characteristics

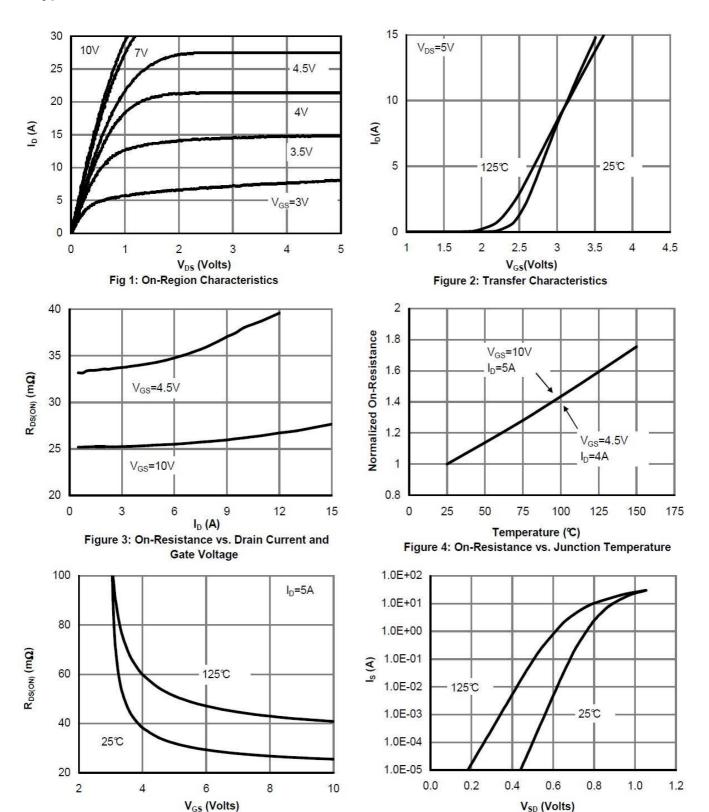
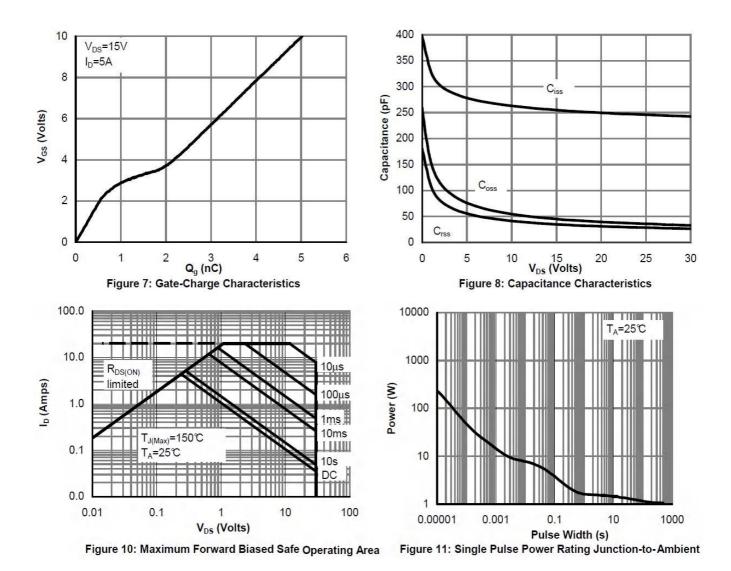


Figure 5: On-Resistance vs. Gate-Source Voltage

Figure 6: Body-Diode Characteristics

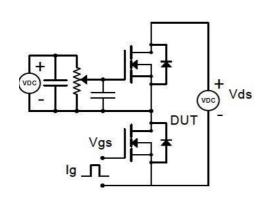


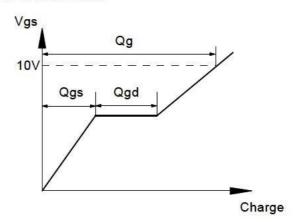
10 In descending order Z_{eJA} Normalized Transient D=0.5, 0.3, 0.1, 0.05, 0.02, 0.01, single pulse $K=T_A+P_{DM}.Z_{\theta JA}.R_{\theta JA}$ Thermal Resistance =125℃/W 0.1 Pn 0.01 Single Pulse T_{on} 0.001 0.00001 0.0001 0.001 0.01 0.1 1000 10 100 1 Pulse Width (s)

Figure 12: Normalized Maximum Transient Thermal Impedance



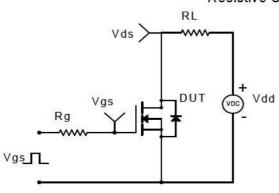
Gate Charge Test Circuit & Waveform

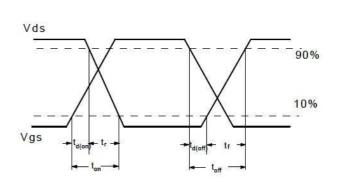




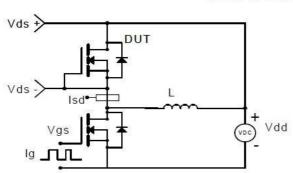
Resistive Switching Test Circuit & Waveforms

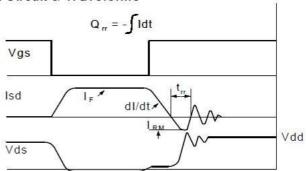
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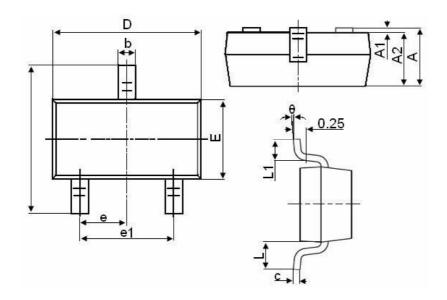


Diode Recovery Test Circuit & Waveforms





SOT-23-3LPackage Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е		0.950TYP	
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



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